

EF Series Power MOSFET With Fast Body Diode



PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. (Ω) at 25 °C	$V_{GS} = 10$ V	0.137
Q_g max. (nC)	38	
Q_{gs} (nC)	10	
Q_{gd} (nC)	6	
Configuration	Single	

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION

Package	PowerPAK® 8 x 8
Lead (Pb)-free and halogen-free	SiHH155N60EF-T1GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	
Continuous drain current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed drain current ^a	I_{DM}	43	
Linear derating factor		1.04	W/°C
Single pulse avalanche energy ^b	E_{AS}	179	mJ
Maximum power dissipation	P_D	156	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Drain-source voltage slope	dv/dt	$T_J = 125$ °C	V/ns
Reverse diode dv/dt ^d			

Notes

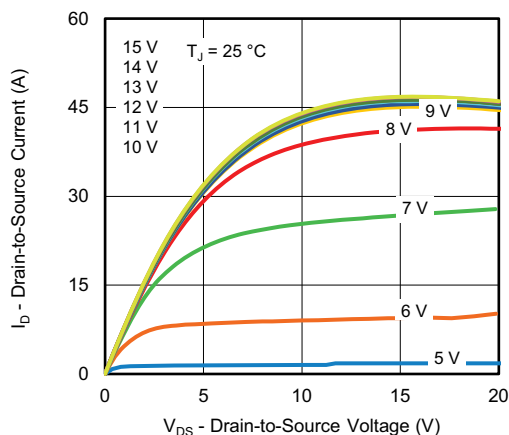
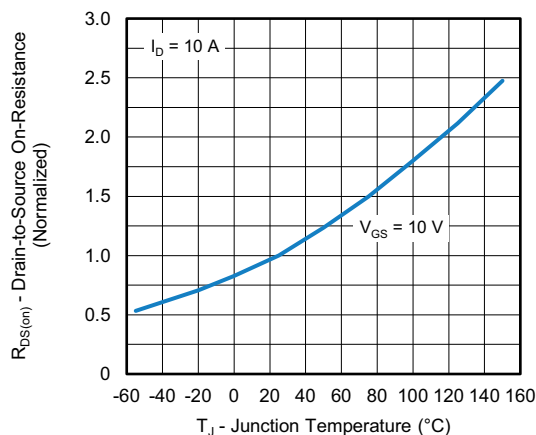
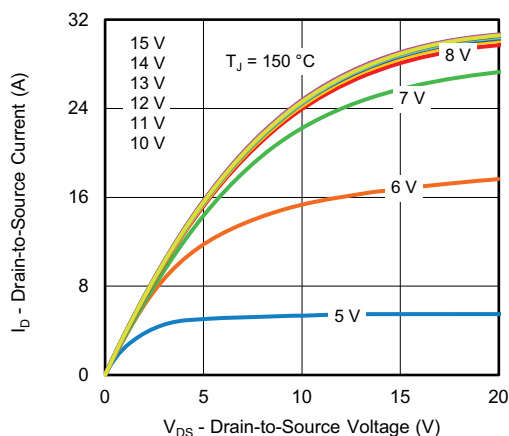
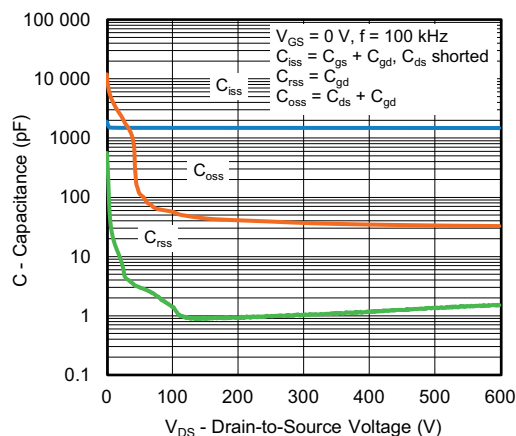
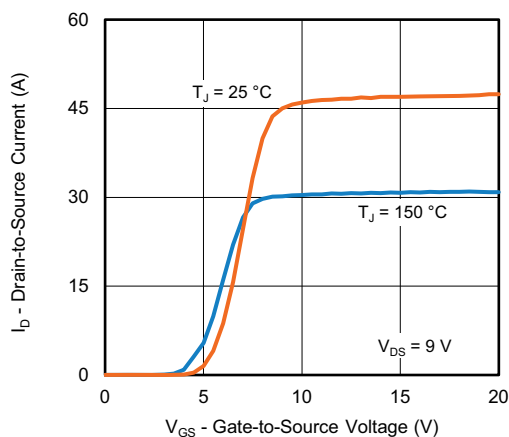
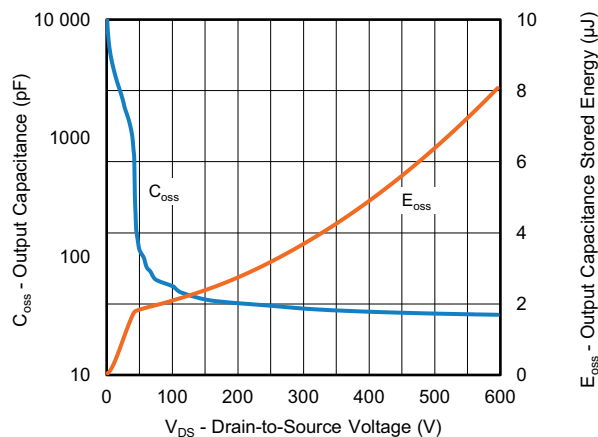
- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 120$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 2.8$ A
- $I_{SD} \leq I_D$, $di/dt = 100$ A/ μ s, starting $T_J = 25$ °C

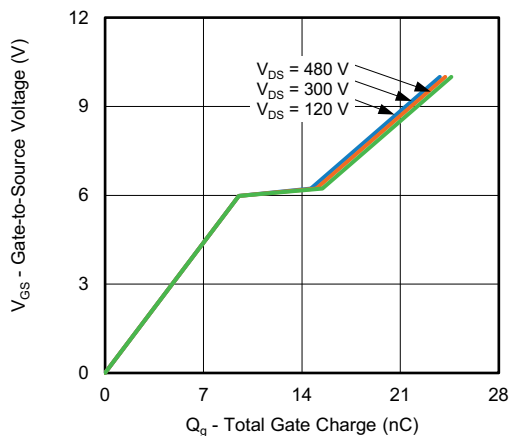
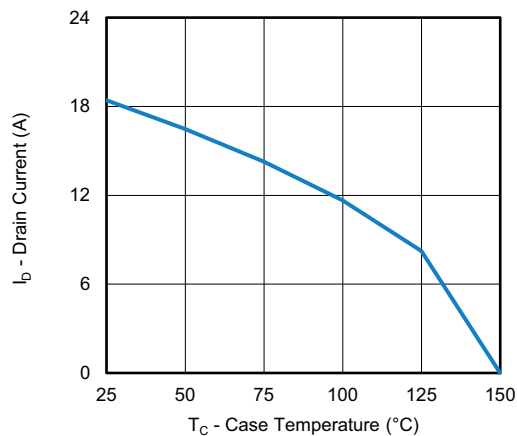
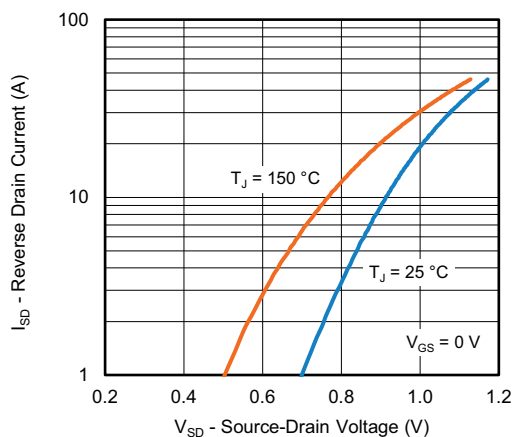
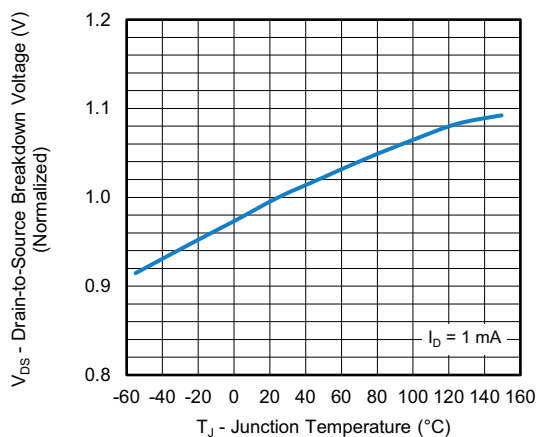
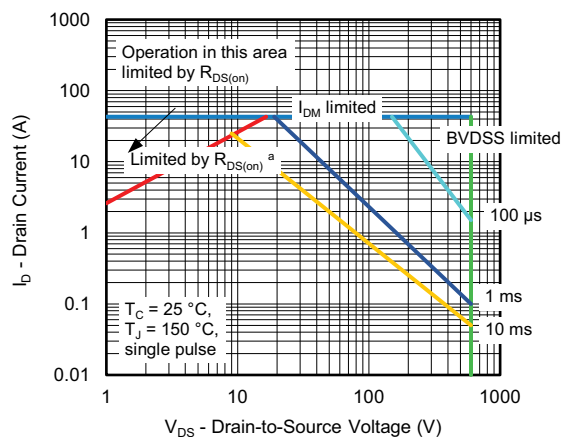
**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	42	55	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.72	0.96	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.62	-	V/°C
Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		3.0	-	5.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 480 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C		-	-	2	mA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.137	0.159	Ω
Forward transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 10 A		-	9.2	-	S
Dynamic							
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 100 KHz		-	1465	-	pF
Output capacitance	C _{Oss}			-	56	-	
Reverse transfer capacitance	C _{rss}			-	1	-	
Effective output capacitance, energy related	C _{O(er)}	V _{DS} = 0 V to 400 V, V _{GS} = 0 V		-	61	-	
Effective output capacitance, time related	C _{O(tr)}			-	356	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 10 A, V _{DS} = 480 V	-	25	38	nC
Gate-source charge	Q _{gs}			-	10	-	
Gate-drain charge	Q _{gd}			-	6	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 480 V, I _D = 10 A, V _{GS} = 10 V, R _g = 9.1 Ω		-	20	40	ns
Rise time	t _r			-	27	54	
Turn-off delay time	t _{d(off)}			-	28	56	
Fall time	t _f			-	17	34	
Gate input resistance	R _g	f = 1 MHz		0.4	0.9	1.8	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	18	A
Pulsed diode forward current	I _{SM}			-	-	43	
Diode forward voltage	V _{SD}	T _J = 25 °C, I _S = 10 A, V _{GS} = 0 V		-	-	1.2	V
Reverse recovery time	t _{rr}	T _J = 25 °C, I _F = I _S = 10 A, di/dt = 100 A/μs, V _R = 400 V		-	95	190	ns
Reverse recovery charge	Q _{rr}			-	0.5	1.0	μC
Reverse recovery current	I _{RRM}			-	12	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 10 - Temperature vs. Drain-to-Source Voltage

Fig. 11 - Maximum Safe Operating Area
Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

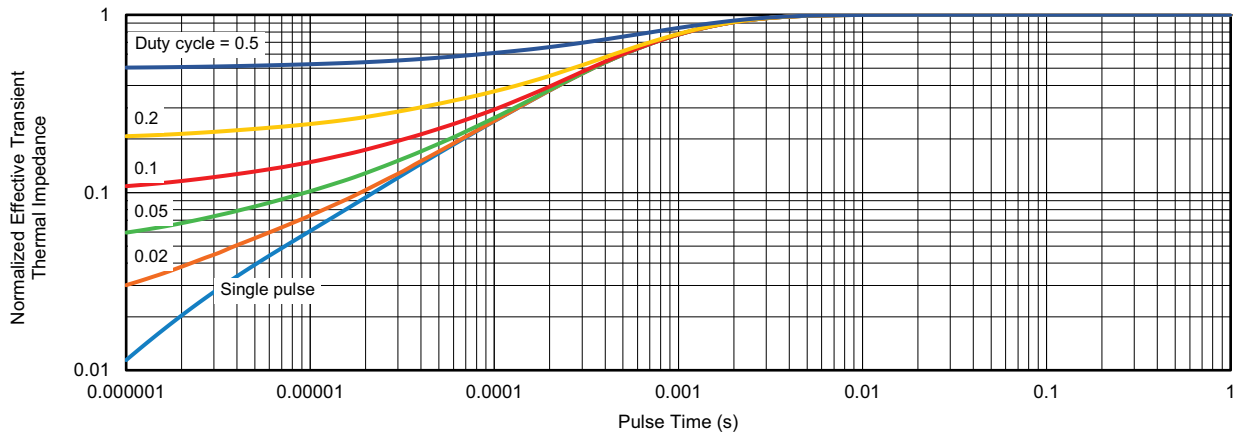


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

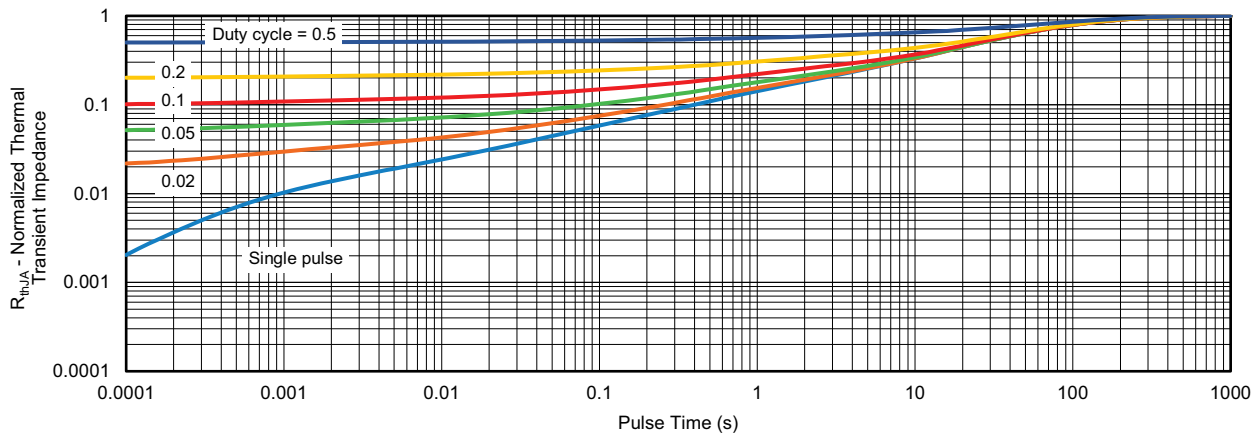
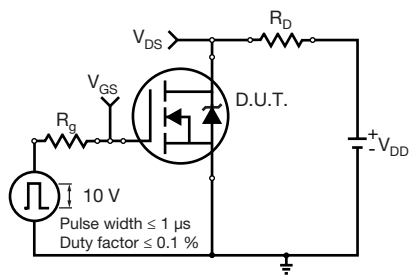
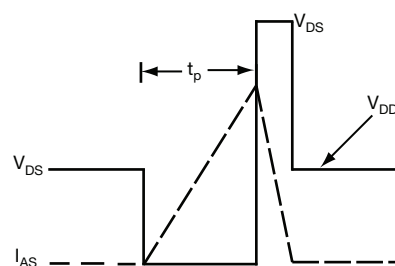
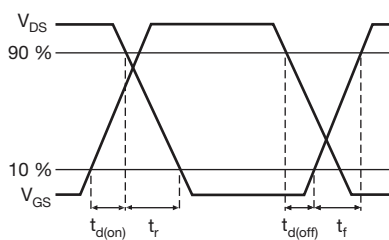
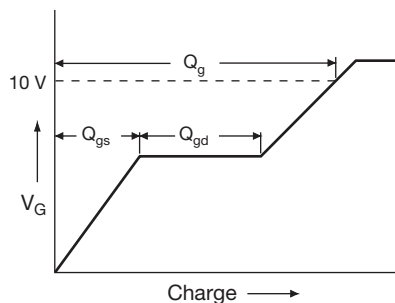
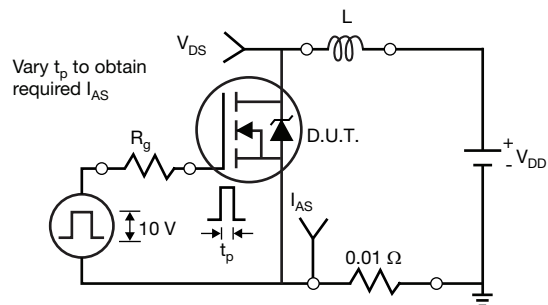
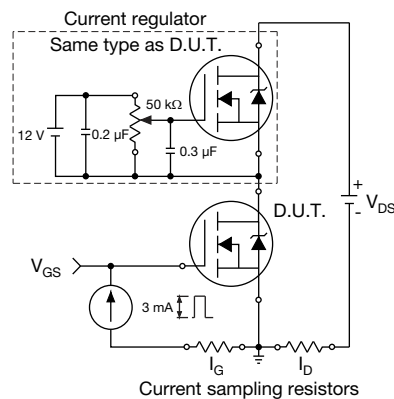


Fig. 13 - Normalized Transient Thermal Impedance, Junction-to-Ambient


Fig. 14 - Switching Time Test Circuit

Fig. 17 - Unclamped Inductive Waveforms

Fig. 15 - Switching Time Waveforms

Fig. 18 - Basic Gate Charge Waveform

Fig. 16 - Unclamped Inductive Test Circuit

Fig. 19 - Gate Charge Test Circuit

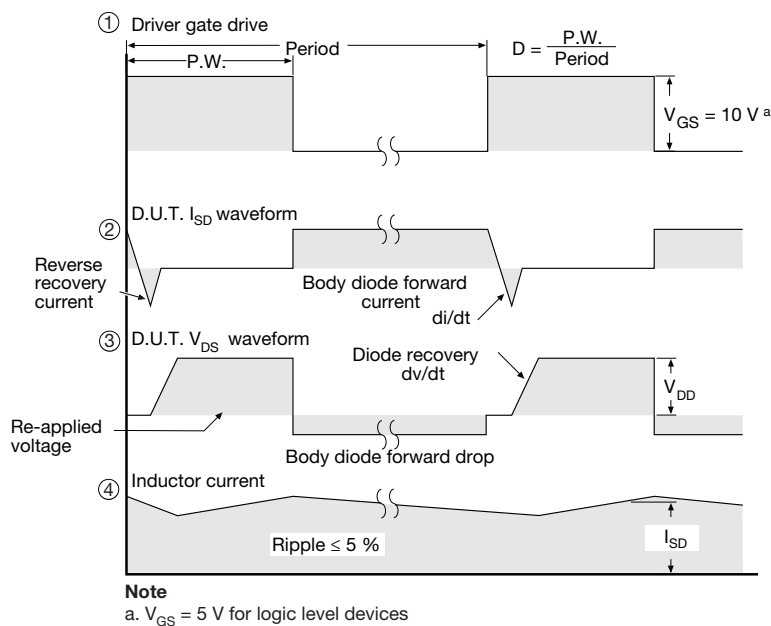


Fig. 20 - For N-Channel

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PowerPAK® 8 x 8 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.95	1.00	1.05	0.037	0.039	0.041
A1	0.00	-	0.05	0.000	-	0.002
A2	020 ref.			0.008 ref.		
b	0.95	1.00	1.05	0.037	0.039	0.041
D	7.90	8.00	8.10	0.311	0.315	0.319
D2	7.10	7.20	7.30	0.280	0.283	0.287
D3	0.40 BSC			0.016 BSC		
e	2.00 BSC			0.079 BSC		
E	7.90	8.00	8.10	0.311	0.315	0.319
E2	4.30	4.35	4.40	0.169	0.171	0.173
E3	0.40 BSC			0.016 BSC		
K	2.75 BSC			0.108 BSC		
L	0.45	0.50	0.55	0.018	0.020	0.022
N ⁽³⁾	8			8		

Notes

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5 M - 1994
- (3) N is the number of terminals
- (4) The pin 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- (5) Exact shape and size of this feature is optional

ECN: E20-0518-Rev. B, 28-Sep-2020
DWG: 6041



Recommended Minimum PADs for PowerPAK® 8 mm x 8 mm



Dimensions in millimeters



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